

isc N-Channel MOSFET Transistor

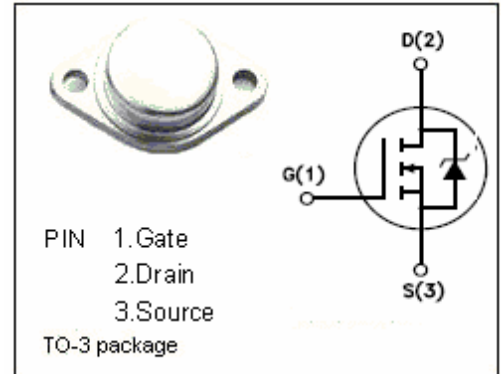
IRF341

DESCRIPTION

- Silicon Gate for Fast Switching Speed
- Rugged

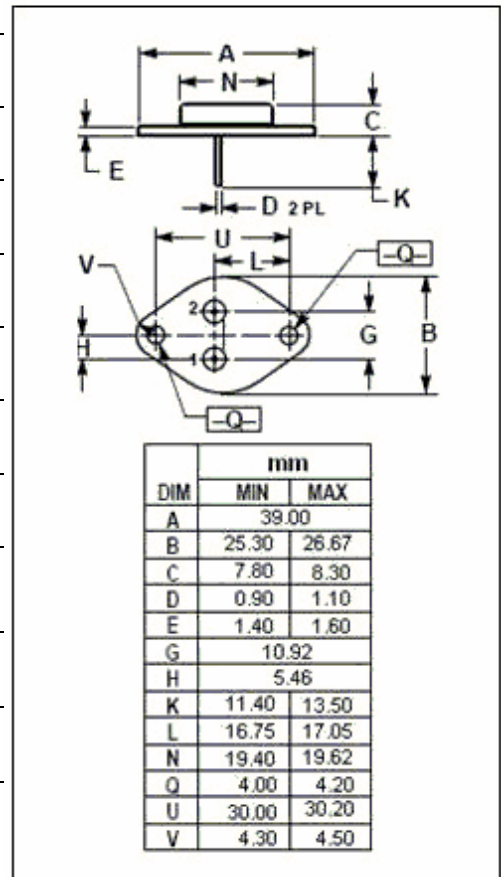
APPLICATIONS

- High voltage
- High speed application



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	350	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=25°C	8	A
P _{tot}	Total Dissipation@TC=25°C	150	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	0.83	°C/W

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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=250\mu\text{A}$	350			V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=250\mu\text{A}$	2.0		4.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}$; $I_D=5.0\text{A}$			0.6	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=150\text{V}$; $V_{GS}=0$			250	μA
V_{SD}	Diode Forward Voltage	$I_S=8.0\text{A}$; $V_{GS}=0$			2.0	V
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}$; $V_{GS}=0\text{V}$; $f_T=1\text{MHz}$			800	pF
C_{rss}	Reverse Transfer Capacitance				150	
C_{oss}	Output Capacitance				450	
t_r	Rise Time	$R_{GS}=12.5\ \Omega$ $I_D=5.0\text{A}$; $V_{DD}=90\text{V}$; $R_L=50\ \Omega$		25		ns
$t_{d(on)}$	Turn-on Telay Time			15		
t_f	Fall Time			20		
$t_{d(off)}$	Turn-off Delay Time			30		